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FEATURES

- * 0.56 inch (14.22 mm) DIGIT HEIGHT
- * CONTINUOUS UNIFORM SEGMENTS
- * LOW POWER REQUIREMENT
- * EXCELLENT CHARACTERS APPEARANCE
- * HIGH BRIGHTNESS & HIGH CONTRAST
- * WIDE VIEWING ANGLE
- * SOLID STATE RELIABILITY
- * CATEGORIZED FOR LUMINOUS INTENSITY

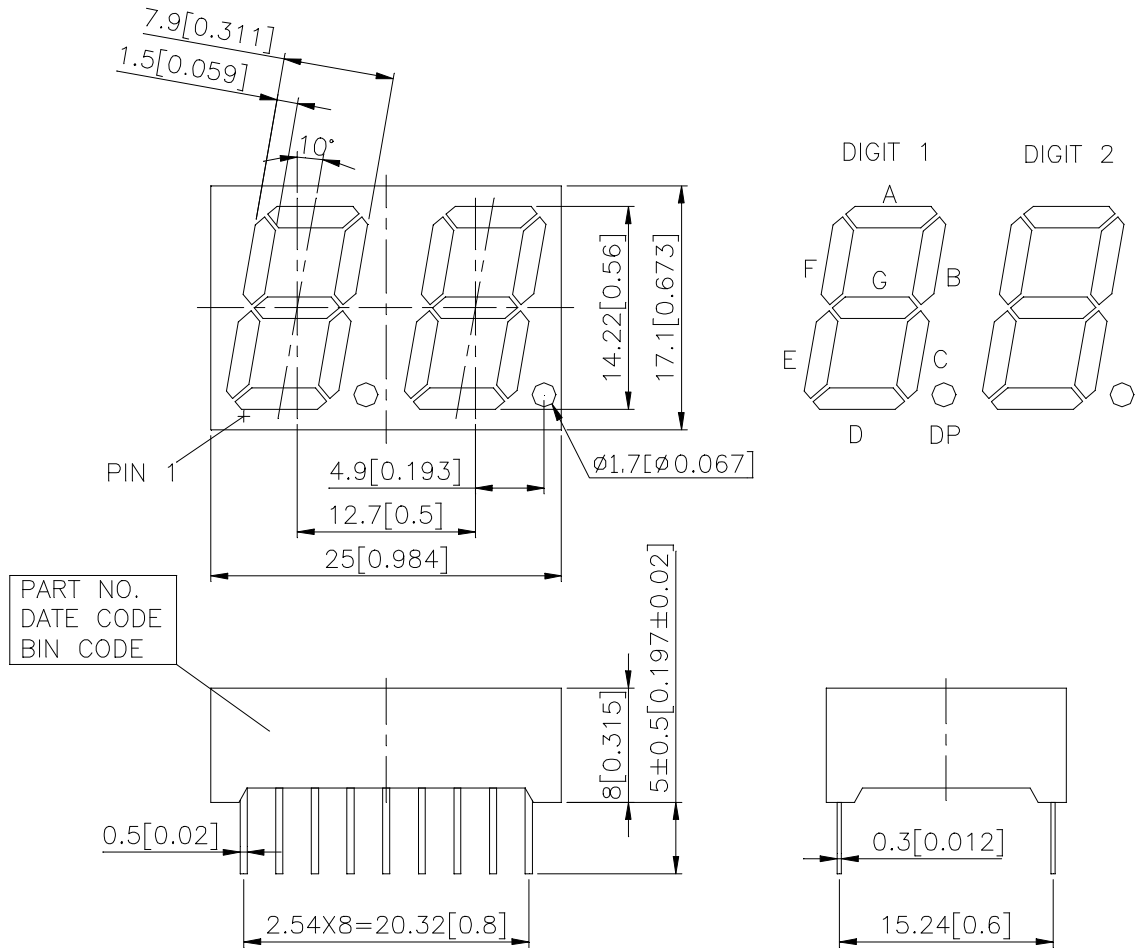
DESCRIPTION

The LTD-5521AE is a 0.56 inch (14.22 mm) digit height dual digit seven-segment display. The device utilizes red orange chips, which are made from GaAsP on a transparent GaP substrate, and has a gray face and white segments.

DEVICE

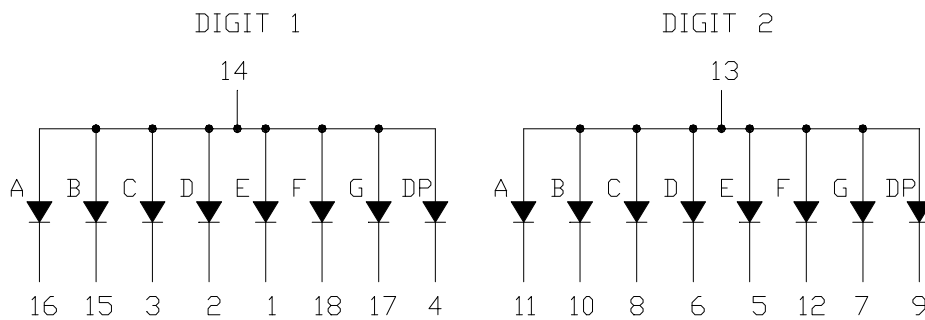
PART NO	DESCRIPTION
Red Orange	COMMON ANODE RT. HAND DECIMAL
LTD-5521AE	

PACKAGE DIMENSIONS



NOTES: All dimensions are in millimeters. Tolerances are ± 0.25 mm unless otherwise noted.

INTERNAL CIRCUIT DIAGRAM



PIN CONNECTION

No.	CONNECTION
1	CATHODE E (DIGIT 1)
2	CATHODE D (DIGIT 1)
3	CATHODE C (DIGIT 1)
4	CATHODE DP (DIGIT 1)
5	CATHODE E (DIGIT 2)
6	CATHODE D (DIGIT 2)
7	CATHODE G (DIGIT 2)
8	CATHODE C (DIGIT 2)
9	CATHODE DP (DIGIT 2)
10	CATHODE B (DIGIT 2)
11	CATHODE A (DIGIT 2)
12	CATHODE F (DIGIT 2)
13	COMMON ANODE (DIGIT 2)
14	COMMON ANODE (DIGIT 1)
15	CATHODE B (DIGIT 1)
16	CATHODE A (DIGIT 1)
17	CATHODE G (DIGIT 1)
18	CATHODE F (DIGIT 1)

ABSOLUTE MAXIMUM RATING AT T_A=25°C

PARAMETER	MAXIMUM RATING	UNIT
Power Dissipation Per Chip	75	mW
Peak Forward Current Per Chip (1/10 Duty Cycle, 0.1ms Pulse Width)	100	mA
Continuous Forward Current Per Chip	25	mA
Derating Linear From 25°C Per Chip	0.33	mA/°C
Reverse Voltage Per Chip	5	V
Operating Temperature Range	-35°C to +85°C	
Storage Temperature Range	-35°C to +85°C	
Solder Temperature: max 260°C for max 3sec at 1.6mm below seating plane		

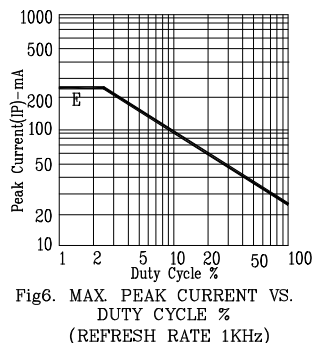
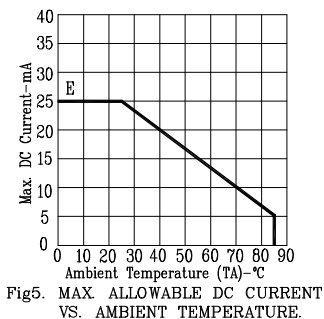
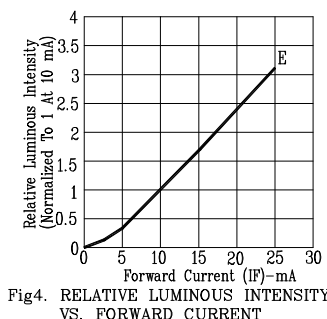
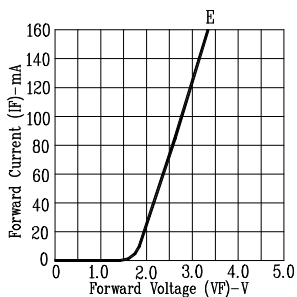
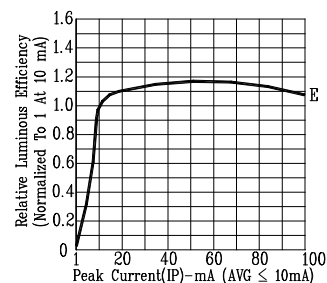
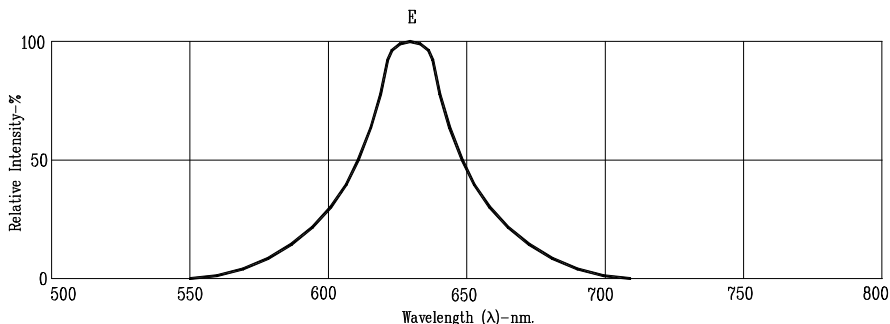
TRICAL / OPTICAL CHARACTERISTICS AT T_A=25°C

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Average Luminous Intensity	I _v	800	2400		μcd	I _F =10mA
Peak Emission Wavelength	λ _p		630		nm	I _F =20mA
Spectral Line Half-Width	Δλ		40		nm	I _F =20mA
Dominant Wavelength	λ _d		621		nm	I _F =20mA
Forward Voltage Per Chip	V _F		2	2.6	V	I _F =20mA
Reverse Current Per Chip	I _R			100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _v -m			2:1		I _F =10mA

Note: Luminous intensity is measured with a light sensor and filter combination that approximates the CIE (Commision Internationale De L'Eclairage) eye-response curve.

TYPICAL ELECTRICAL / OPTICAL CHARACTERISTIC CURVES

(25°C Ambient Temperature Unless Otherwise Noted)



NOTE: E=RED ORANGE